

Electrostatic Discharged Protection Devices (ESD) Data Sheet

Description

Brightking's LES08CXXL04 series has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by electrostatic discharge (ESD), electrical fast transients (EFT), and lightning.

The low capacitance array configuration of the series allows the user to protect four high-speed data or I/O lines. The high surge capability makes the series suitable for telecommunication systems operating in harsh transient environments. The low inductance construction minimizes voltage overshoot during high current surges.

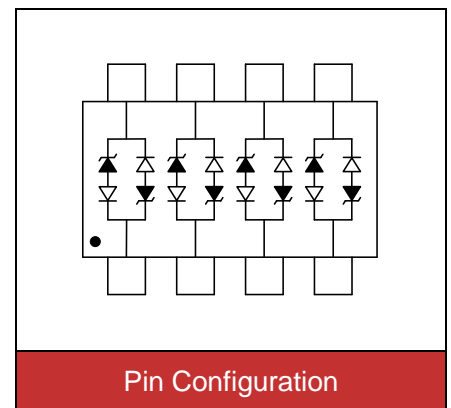


Contact : ±30kV
Air : ±30kV



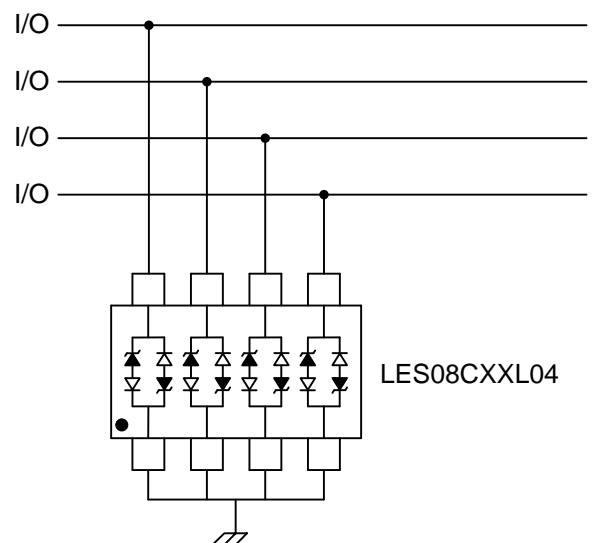
Features

- IEC61000-4-2 ESD 30KV Air, 30KV contact compliance
- SOIC-08 surface mount package
- Protects four I/O lines
- Peak power dissipation of 500W under 8/20µs waveform
- Working voltage: 5V, 12V, 15V and 24V
- Low leakage current
- Low capacitance and clamping voltage
- Solid-state silicon avalanche technology
- Lead Free/RoHS compliant
- Solder reflow temperature: Pure Tin-Sn, 260~270°C
- Flammability rating UL 94V-0
- Meets MSL level 1, per J-STD-020



Applications

- Multi-Mode transceiver protection
- WAN equipment
- CSU/DSU
- Multiplexers
- Routers
- RS-232 (V.28)
- RS-422 (V.11, X.21)
- Ethernet-10/100 base T
- Low-voltage ASICs



Maximum Ratings

Rating	Symbol	Value	Unit
Peak pulse power (tp=8/20μs waveform)	P _{PP}	500	W
ESD voltage (Contact discharge)	V _{ESD}	±30	kV
ESD voltage (Air discharge)		±30	
Storage & operating temperature range	T _{STG} , T _J	-55~+150	°C

Electrical Characteristics (T_J=25°C)

LES08C05L04 (Marking: B LC03C-4)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V _{RWM}				3.3	V
Reverse breakdown voltage	V _{BR}	I _{BR} =1mA	4.5			V
Reverse leakage current	I _R	V _R =3.3V each I/O pin			40	μA
Clamping voltage (tp=8/20μs)	V _C	I _{PP} =1A			7	V
Clamping voltage (tp=8/20μs)	V _C	I _{PP} =10A			15	V
Off state junction capacitance	C _J	0Vdc, f=1MHz Between I/O pins and GND			15	pF

LES08C05L04 (Marking: B LC05C-4)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V _{RWM}				5	V
Reverse breakdown voltage	V _{BR}	I _{BR} =1mA	6			V
Reverse leakage current	I _R	V _R =5V each I/O pin			10	μA
Clamping voltage (tp=8/20μs)	V _C	I _{PP} =1A			9.8	V
Clamping voltage (tp=8/20μs)	V _C	I _{PP} =10A			17	V
Off state junction capacitance	C _J	0Vdc, f=1MHz Between I/O pins and GND			15	pF

LES08C12L04 (Marking: B LC12C-4)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				12	V
Reverse breakdown voltage	V_{BR}	$I_{BR}=1mA$	13.4			V
Reverse leakage current	I_R	$V_R=12V$ each I/O pin			1	μA
Clamping voltage ($t_p=8/20\mu s$)	V_C	$I_{PP}=1A$			19	V
Clamping voltage ($t_p=8/20\mu s$)	V_C	$I_{PP}=10A$			25	V
Off state junction capacitance	C_J	0Vdc, f=1MHz Between I/O pins and GND			15	pF

LES08C15L04 (Marking: B LC15C-4)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				15	V
Reverse breakdown voltage	V_{BR}	$I_{BR}=1mA$	16.7			V
Reverse leakage current	I_R	$V_R=15V$ each I/O pin			1	μA
Clamping voltage ($t_p=8/20\mu s$)	V_C	$I_{PP}=1A$			24	V
Clamping voltage ($t_p=8/20\mu s$)	V_C	$I_{PP}=10A$			30	V
Off state junction capacitance	C_J	0Vdc, f=1MHz Between I/O pins and GND			15	pF

Electrical Characteristics ($T_J=25^\circ C$)
LES08C24L04 (Marking: B LC24C-4)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V_{RWM}				24	V
Reverse breakdown voltage	V_{BR}	$I_{BR}=1mA$	26.7			V
Reverse leakage current	I_R	$V_R=24V$ each I/O pin			1	μA
Clamping voltage ($t_p=8/20\mu s$)	V_C	$I_{PP}=1A$			43	V
Clamping voltage ($t_p=8/20\mu s$)	V_C	$I_{PP}=10A$			49	V
Off state junction capacitance	C_J	0Vdc, f=1MHz Between I/O pins and GND			15	pF

Typical Characteristics Curves

Figure 1. Power Derating Curve

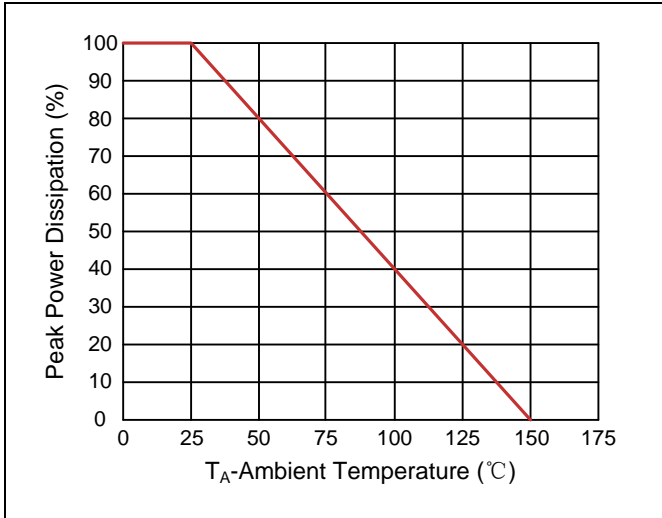


Figure 2. Pulse Waveforms

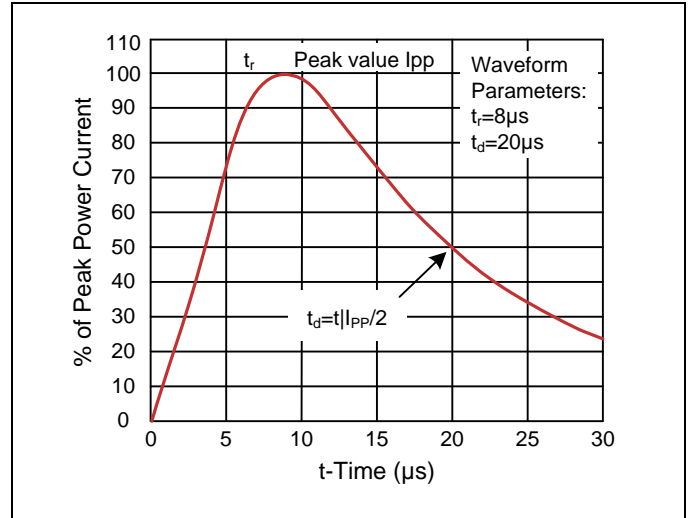


Figure 3. Non-Repetitive Peak Pulse vs. Pulse Time

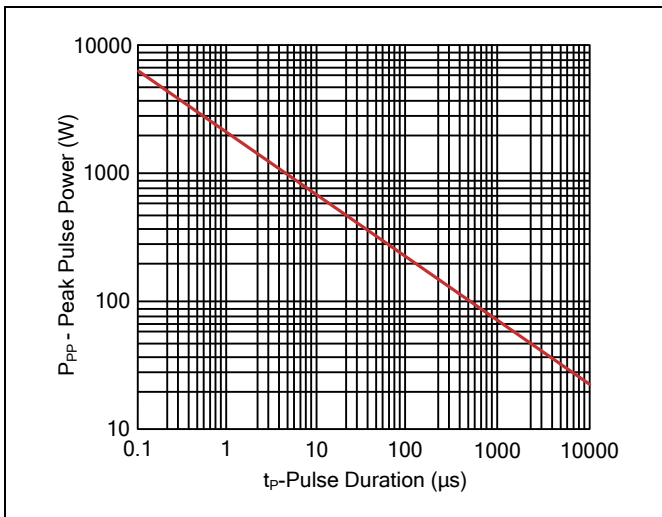
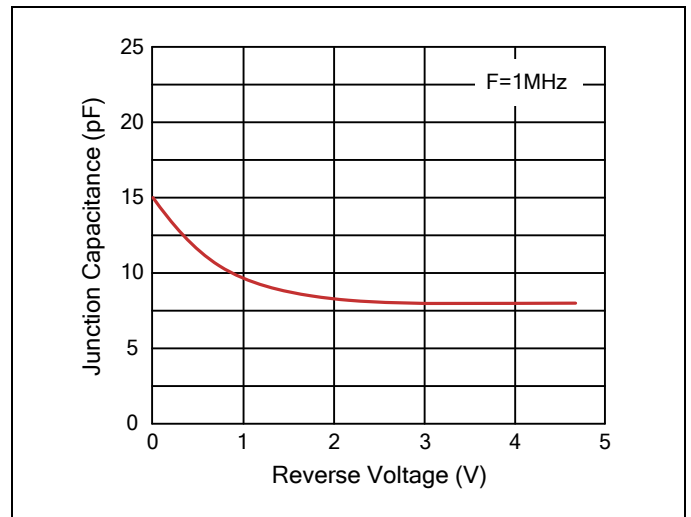
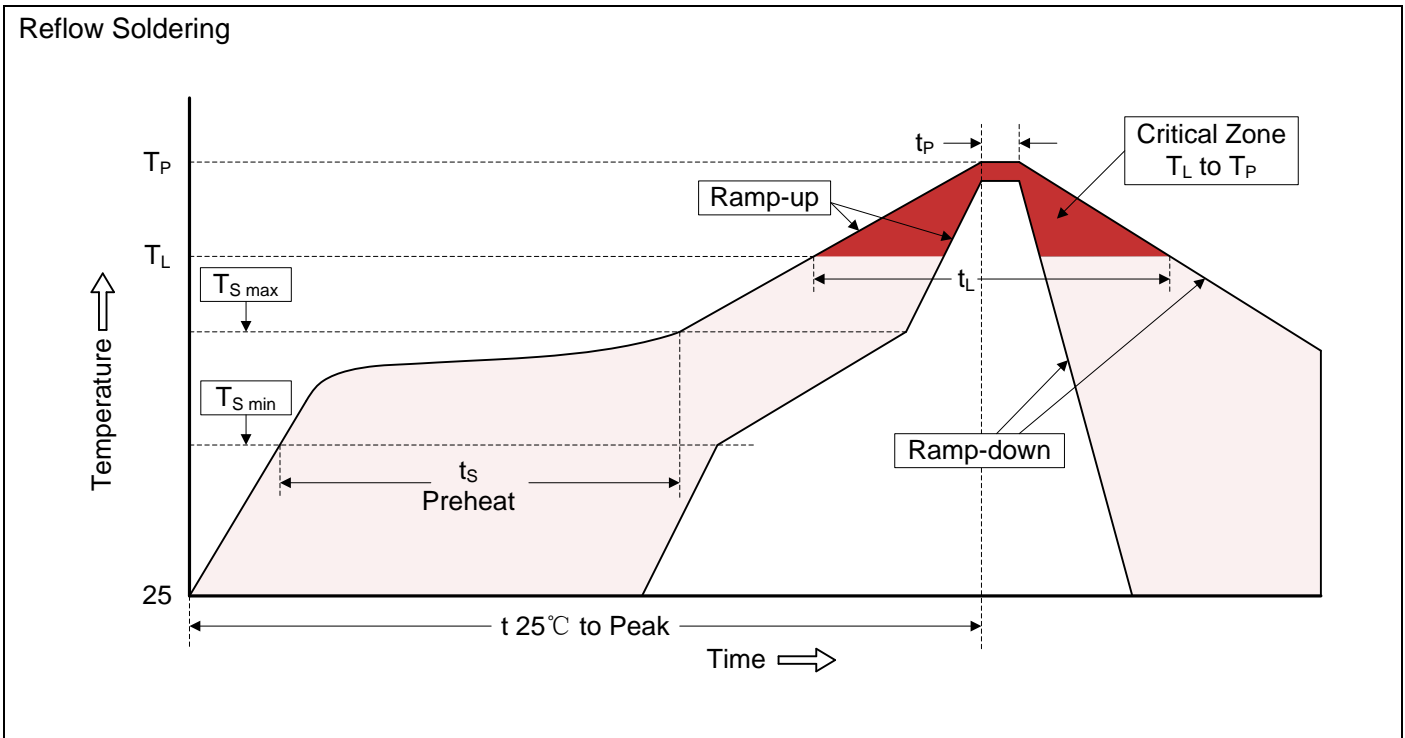


Figure 4. Capacitance vs. Reverse Voltage



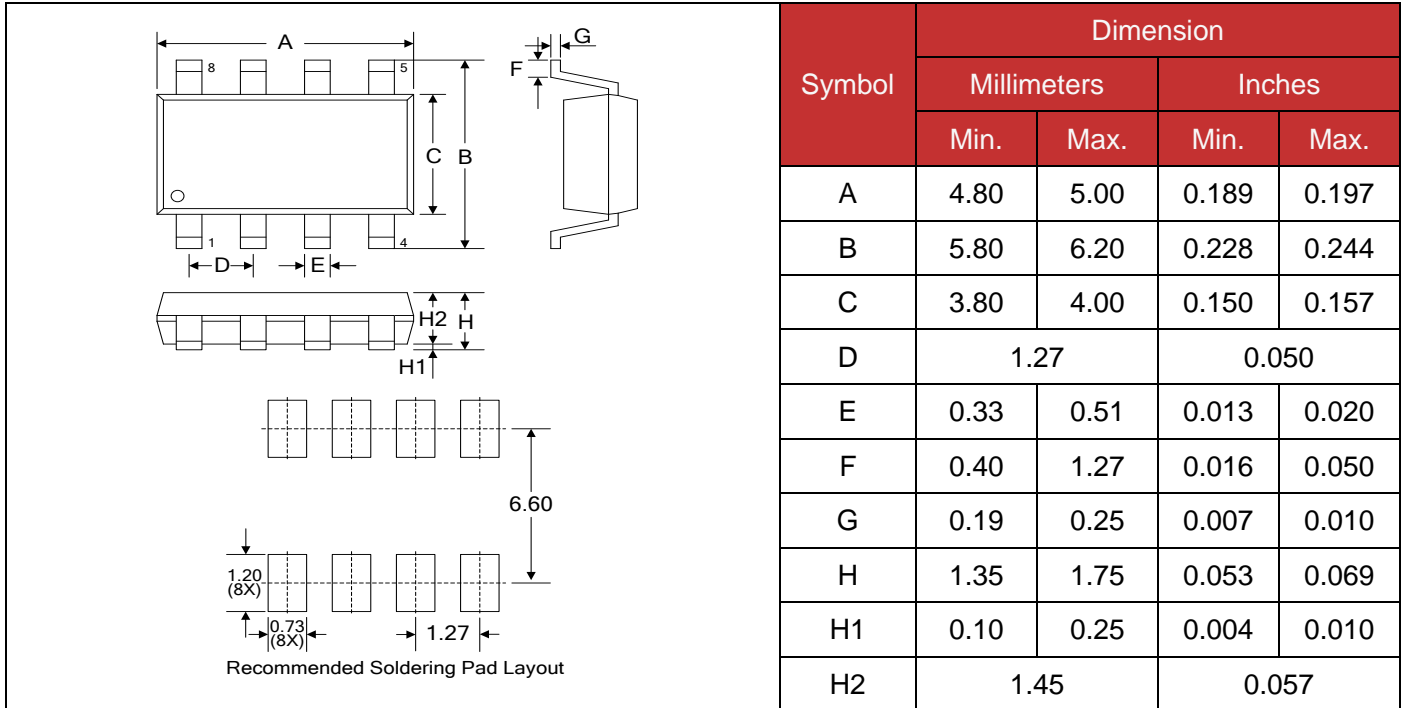
Recommended Soldering Conditions



Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.
Preheat -Temperature Min ($T_{S\ min}$) -Temperature Max ($T_{S\ max}$) -Time (min to max) (t_s)	150°C 200°C 60-180 seconds
$T_{S\ max}$ to T_L -Ramp-up Rate	3°C/second max.
Time maintained above: -Temperature (T_L) -Time (t_L)	217°C 60-150 seconds
Peak Temperature (T_P)	260°C
Time within 5°C of actual Peak Temperature (t_P)	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Dimensions (SOIC-08)



Packaging

